

# **Isc N-Channel MOSFET Transistor**

# WFD5N65L

### • FEATURES

- · With To-252(DPAK) package
- · Low input capacitance and gate charge
- · Low gate input resistance
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



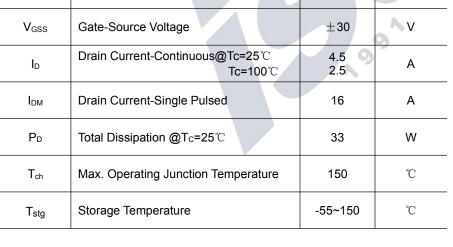
## APPLICATIONS

Switching applications



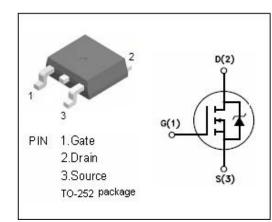
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

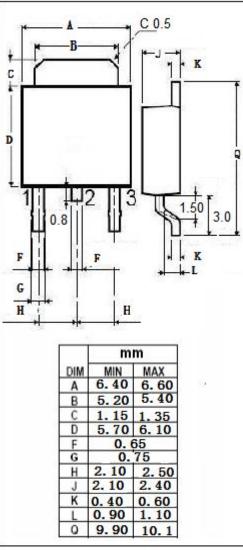
| SYMBOL           | PARAMETER                                  | VALUE      | UNIT          |
|------------------|--|------------|---------------|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 650        | V             |
| V <sub>GSS</sub> | Gate-Source Voltage                        | ±30        | V             |
| I <sub>D</sub>   | Drain Current-Continuous@Tc=25℃<br>Tc=100℃ | 4.5<br>2.5 | А             |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | 16         | А             |
| P <sub>D</sub>   | Total Dissipation @Tc=25℃                  | 33         | W             |
| $T_ch$           | Max. Operating Junction Temperature        | 150        | ${\mathbb C}$ |
| T <sub>stg</sub> | Storage Temperature                        | -55~150    | ${\mathbb C}$ |



### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                                     |     | UNIT |  |
|-----------|---|-----|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance            | 2.5 | °C/W |  |
| Rth(ch-a) | h(ch-a) Channel-to-ambient thermal resistance |     | °C/W |  |





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25°C unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS  | MIN | ТҮР | MAX  | UNIT |
|---------------------|--------------------------------|---|-----|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA              | 650 |     |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA | 2.0 |     | 4.0  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =2A                 |     | 2.1 | 2.5  | Ω    |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> =±30V;V <sub>DS</sub> = 0V                |     |     | ±0.1 | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =650V; V <sub>GS</sub> = 0V               |     |     | 10   | μА   |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =4.5A, V <sub>GS</sub> = 0 V              |     |     | 1.4  | V    |

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